

MH25609J-85,-10,-12,-15/ MH25609JA-85,-10,-12,-15

PAGE MODE 262144-WORD BY 9-BIT DYNAMIC RAM

DESCRIPTION

The MH25609J, JA is 262144 word x 9 bit dynamic RAM and consists of nine industry standard 256K x 1 dynamic RAMs in plastic leaded chip carrier.

The mounting of plastic leaded chip carrier on a single in-line package provides any application where high densities and large quantities of memory are required.

MH25609JA is a leaded type-memory module, allowing direct insertion to normal through-hole-board like DIP devices.

MH25609J is a socket type-memory module, suitable for easy interchanging or addition of modules.

FEATURES

- High-speed

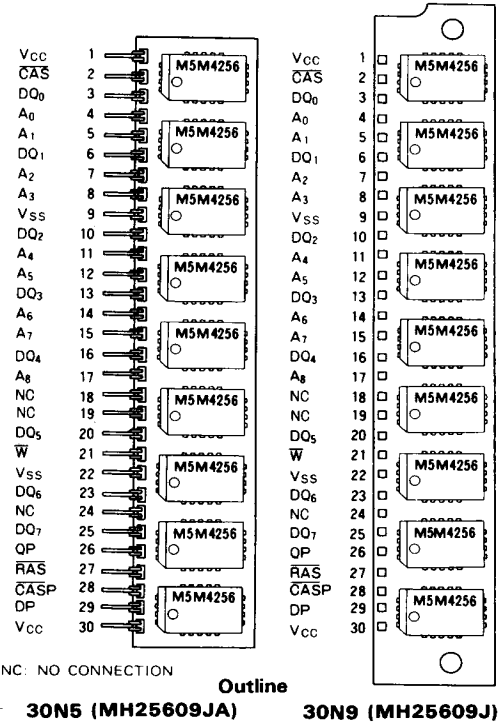
Type name	Access time (max) (ns)	Cycle time (min) (ns)	Power dissipation (typ) (mW)
MH25609J-85 MH25609JA-85	85	160	2700
MH25609J-10 MH25609JA-10	100	190	2340
MH25609J-12 MH25609JA-12	120	220	2070
MH25609J-15 MH25609JA-15	150	260	1800

- Utilizes industry standard 256K RAMs in plastic leaded carriers
- 30 pins Single In-line Package
- Single +5V ($\pm 10\%$) supply operation
- Low standby power dissipation 225mW (max)
- Low operation power dissipation.
 - MH25609J-85/MH25609JA-85 3.47W (max)
 - MH25609J-10/MH25609JA-10 3.24W (max)
 - MH25609J-12/MH25609JA-12 2.97W (max)
 - MH25609J-15/MH25609JA-15 2.75W (max)
- All inputs are directly TTL compatible
- All outputs are three-state and directly TTL compatible
- Includes (0.15 μ F x 9) decoupling capacitors
- 256 refresh cycles every 4ms, A₈ Pin is not need for refresh
- Common $\overline{\text{CAS}}$ control for eight common Data-In and Data-Out lines.
- Separate $\overline{\text{CAS}}$ ($\overline{\text{CASP}}$) control for one separate pair of Data-In and Data-Out lines.
- The common I/O feature dictates the use of only early write operation to prevent contention on Data-In and Data-Out.
- Bit nine (DP, QP) controlled by $\overline{\text{CASP}}$ is generally used for parity.

APPLICATION

Main memory unit for computers, Microcomputer memory

PIN CONFIGURATION (TOP VIEW)



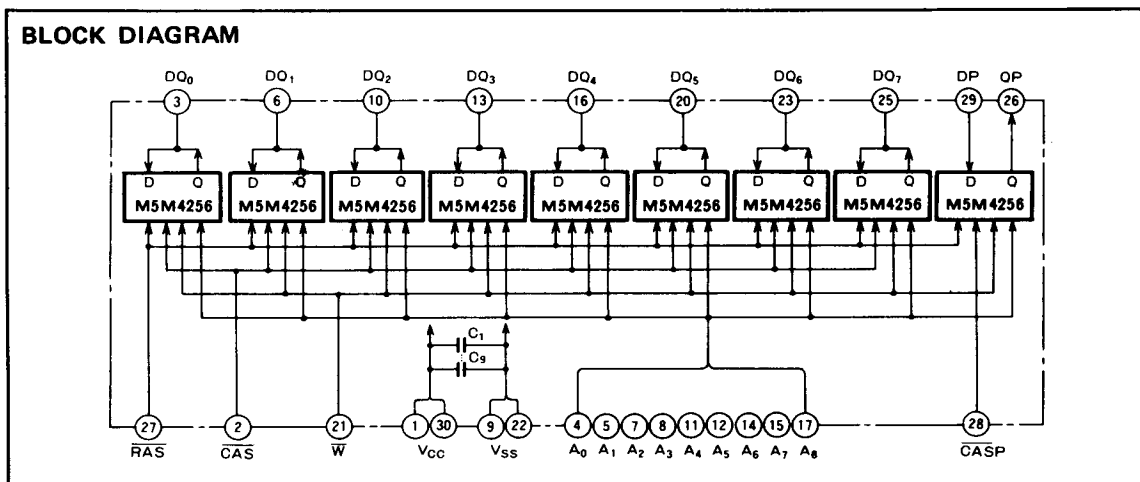
FUNCTION

The MH25609J, JA provides, in addition to normal read and early write operations, a number of other functions, e.g., page mode, RAS-only refresh, hidden refresh and CAS before RAS refresh. The input conditions for each are shown in Table 1.

Table 1 Input conditions for each mode

Operation	Inputs						Output	Refresh
	$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{W}}$	D	Row address	Column address	Q	
Read	ACT	ACT	NAC	DNC	APD	APD	VLD	YES
Early write	ACT	ACT	ACT	VLD	APD	APD	OPN	YES
$\overline{\text{RAS}}$ -only refresh	ACT	NAC	DNC	DNC	APD	DNC	OPN	YES
Hidden refresh	ACT	ACT	DNC	DNC	DNC	DNC	VLD	YES
$\overline{\text{CAS}}$ before RAS refresh	ACT	ACT	DNC	DNC	DNC	DNC	OPN	YES
Standby	NAC	DNC	DNC	DNC	DNC	DNC	OPN	NO

Note: ACT: active, NAC: nonactive, DNC: don't care, VLD: valid, APD: applied, OPN: open.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage	With respect to V _{SS}	-1 ~ 7	V
V _I	Input voltage		-1 ~ 7	V
V _O	Output voltage		-1 ~ 7	V
I _O	Output current		50	mA
P _d	Power dissipation	T _a = 25°C	9	W
T _{opr}	Operating temperature		0 ~ 70	°C
T _{stg}	Storage temperature		-40 ~ 125	°C

RECOMMENDED OPERATING CONDITIONS (T_a = 0 ~ 70°C, unless otherwise noted) (Note 1)

Symbol	Parameter	Limits			Unit
		Min	Nom	Max	
V _{CC}	Supply voltage	4.5	5	5.5	V
V _{SS}	Supply voltage	0	0	0	V
V _{IH}	High-level input voltage, all inputs	2.4		6.5	V
V _{IL}	Low-level input voltage all inputs	-2		0.8	V

Note 1: All voltage values are with respect to V_{SS}.

ELECTRICAL CHARACTERISTICS (T_a = 0 ~ 70°C, V_{CC} = 5V ± 10%, V_{SS} = 0V, unless otherwise noted) (Note 2)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
V _{OH}	High-level output voltage	I _{OH} = -5mA	2.4		V _{CC}	V	
V _{OL}	Low-level output voltage	I _{OL} = 4.2mA	0		0.4	V	
I _{OZ}	Off-state output current	0 floating 0V ≤ V _{OUT} ≤ 5.5V	-20		20	μA	
I _I	Input current	0V ≤ V _{IN} ≤ V _{CC} , Other input pins = 0V	-90		90	μA	
I _{CC1(AV)}	Average supply current from V _{CC} , operating (Note 3, 4)	R _{AS} , C _{AS} cycling t _{CR} = t _{CW} = min, output open			630	mA	
					585		
					540		
					495		
I _{CC2}	Supply current from V _{CC} , standby	R _{AS} = C _{AS} = V _{IH} output open			40.5	mA	
I _{CC3(AV)}	Average supply current from V _{CC} , refreshing (Note 3)	R _{AS} cycling C _{AS} = V _{IH} t _{C(RAS)} = min, output open			540	mA	
					495		
					450		
					405		
I _{CC4(AV)}	Average supply current from V _{CC} , page mode (Note 3, 4)	R _{AS} = V _{IL} , C _{AS} cycling t _{CPG} = min, output open			495	mA	
					450		
					405		
					360		
I _{CC6(AV)}	Average supply current from V _{CC} , automatic refreshing (Note 3)	C _{AS} before R _{AS} refresh cycling t _{O(RAS)} = min, output open			585	mA	
					540		
					495		
					450		
C _{I(A)}	Input capacitance, address inputs	V _I = V _{SS} f = 1MHz V _I = 25mVrms			60	pF	
C _{I(DO)}	Data input/data output capacitance				17	pF	
C _{I(W)}	Input capacitance, write control input				75	pF	
C _{I(RAS)}	Input capacitance, R _{AS} input				75	pF	
C _{I(CAS)}	Input capacitance, C _{AS} input				70	pF	
C _{I(CASP)}	Input capacitance, C _{ASP} input				13	pF	
C _{I(DP)}	Input capacitance				17	pF	
C _{O(OP)}	Output capacitance		V _O = V _{SS} , f = 1MHz, V _I = 25mVrms			12	pF

- Note 2: 1. Current flowing into an IC is positive, out is negative.
 3. I_{CC1(AV)}, I_{CC3(AV)}, I_{CC4(AV)} and I_{CC6(AV)} are dependent on cycle rate. Maximum current is measured at the fastest cycle rate.
 4. I_{CC1(AV)} and I_{CC4(AV)} are dependent on output loading. Specified values are obtained with the output open.



TIMING REQUIREMENTS (For Read, Early Write, Refresh, and Page-Mode Cycle)

($T_a = 0 \sim 70^\circ\text{C}$, $V_{CC} = -5\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$, unless otherwise noted, See notes 5, 6 and 7)

Symbol	Parameter	Alternative Symbol	Limits								Unit
			MH25609-85		MH25609-10		MH25609-12		MH25609-15		
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{CRF}	Refresh cycle time	t_{REF}		4		4		4		4	ms
$t_{W(RASH)}$	\overline{RAS} high pulse width	t_{RP}	65		80		90		100		ns
$t_{W(RASL)}$	\overline{RAS} low pulse width	t_{RAS}	85	10000	100	10000	120	10000	150	10000	ns
$t_{W(CASL)}$	\overline{CAS} low pulse width	t_{CAS}	45	10000	50	10000	60	10000	75	10000	ns
$t_{W(CASH)}$	\overline{CAS} high pulse width (Note 8)	t_{CPN}	20		20		25		25		ns
$t_{h(RAS-CAS)}$	\overline{CAS} hold time after \overline{RAS}	t_{CSH}	85		100		120		150		ns
$t_{h(CAS-RAS)}$	\overline{RAS} hold time after \overline{CAS}	t_{RSH}	45		50		60		75		ns
$t_{d(CAS-RAS)}$	Delay time, \overline{CAS} to \overline{RAS} (Note 9)	t_{CRP}	10		10		10		10		ns
$t_{d(RAS-CAS)}$	Delay time, \overline{RAS} to \overline{CAS} (Note 10)	t_{RCD}	15	40	15	50	20	60	25	75	ns
$t_{SU(RA-RAS)}$	Row address setup time before \overline{RAS}	t_{ASR}	0		0		0		0		ns
$t_{SU(CA-CAS)}$	Column address setup time before \overline{CAS}	t_{ASC}	-5		-5		-5		-5		ns
$t_{h(RAS-RA)}$	Row address hold time after \overline{RAS}	t_{RAH}	10		10		15		20		ns
$t_{h(RAS-CA)}$	Column address hold time after \overline{CAS}	t_{CAH}	15		15		20		25		ns
$t_{h(RAS-CA)}$	Column address hold time after \overline{RAS}	t_{AR}	55		65		80		100		ns
t_{THL}	Transition time	t_T	3	50	3	50	3	50	3	50	ns
t_{TLH}			3	50	3	50	3	50	3	50	ns

- Note 5. An initial pause of 500 μ s is required after power-up followed by any eight \overline{RAS} or $\overline{RAS}/\overline{CAS}$ cycles before proper device operation is achieved.
 6. The switching characteristics are defined at $t_{THL} = t_{TLH} = 5\text{ns}$.
 7. Reference levels of input signals are $V_{IH\ min}$ and $V_{IL\ max}$. Reference levels for transition time are also between V_{IH} and V_{IL} .
 8. Except for page-mode.
 9. $t_{d(CAS-RAS)}$ requirement is only applicable for all $\overline{RAS}/\overline{CAS}$ cycles.
 10. Operation within the $t_{d(RAS-CAS)}$ max limit insures that $t_{d(RAS)}$ max can be met, $t_{d(RAS-CAS)}$ max is specified reference point only; if $t_{d(RAS-CAS)}$ is greater than the specified $t_{d(RAS-CAS)}$ max limit, then access time is controlled exclusively by $t_{d(CAS)}$.
 $t_{d(RAS-CAS)}\ min = t_{h(RAS-RA)}\ min + 2t_{THL}(t_{THL}) + t_{su(CA-CAS)}\ min$.

SWITCHING CHARACTERISTICS ($T_a = 0 \sim 70^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$, unless otherwise noted)

Read Cycle

Symbol	Parameter	Alternative Symbol	Limits								Unit
			MH25609-85		MH25609-10		MH25609-12		MH25609-15		
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{CR}	Read cycle time	t_{RC}	160		190		220		260		ns
$t_{SU(R-CAS)}$	Read setup time before \overline{CAS}	t_{RCS}	0		0		0		0		ns
$t_{h(CAS-R)}$	Read hold time after \overline{CAS} (Note 11)	t_{RCH}	0		0		0		0		ns
$t_{h(RAS-R)}$	Read hold time after \overline{RAS} (Note 11)	t_{RRH}	10		10		10		10		ns
$t_{dis(CAS)}$	Output disable time (Note 12)	t_{OFF}	0	20	0	25	0	30	0	35	ns
$t_{a(CAS)}$	\overline{CAS} access time (Note 13)	t_{CAC}		45		50		60		75	ns
$t_{a(RAS)}$	\overline{RAS} access time (Note 14)	t_{RAC}		85		100		120		150	ns

- Note 11. Either $t_{h(RAS-R)}$ or $t_{h(CAS-R)}$ must be satisfied for a read cycle.
 12. $t_{dis(CAS)}$ max defines the time at which the output achieves the open circuit condition and is not reference to V_{OH} or V_{OL} .
 13. This is the value when $t_{d(RAS-CAS)} \geq t_{d(RAS-CAS)}\ max$. Test conditions; Load = 2TTL, $C_L = 100\text{pF}$.
 14. This is the value when $t_{d(RAS-CAS)} < t_{d(RAS-CAS)}\ max$. When $t_{d(RAS-CAS)} \geq t_{d(RAS-CAS)}\ max$, $t_{a(RAS)}$ will increase by the amount that $t_{d(RAS-CAS)}$ exceeds the value shown. Test conditions; Load = 2TTL, $C_L = 100\text{pF}$.

Write Cycle

Symbol	Parameter	Alternative Symbol	Limits								Unit
			MH25609-85		MH25609-10		MH25609-12		MH25609-15		
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{CW}	Write cycle time	t_{RC}	160		190		220		260		ns
$t_{SU(W-CAS)}$	Write setup time before \overline{CAS} (Note 15)	t_{WCS}	-10		-10		-10		-10		ns
$t_{h(CAS-W)}$	Write hold time after \overline{CAS}	t_{WCH}	15		20		25		30		ns
$t_{h(RAS-W)}$	Write hold time after \overline{RAS}	t_{WCR}	55		70		85		105		ns
$t_{h(W-RAS)}$	\overline{RAS} hold time after write	t_{RWL}	30		35		40		45		ns
$t_{h(W-CAS)}$	\overline{CAS} hold time after write	t_{CWL}	30		35		40		45		ns
$t_{W(W)}$	Write pulse width	t_{WP}	15		20		25		30		ns
$t_{SU(D-CAS)}$	Data-in setup time before \overline{CAS}	t_{DS}	0		0		0		0		ns
$t_{h(CAS-D)}$	Data-in hold time after \overline{CAS}	t_{DH}	15		20		25		30		ns
$t_{h(RAS-D)}$	Data-in hold time after \overline{RAS}	t_{DHR}	55		70		85		105		ns

Note 15. When $t_{su(W-CAS)} < t_{su(W-CAS)}\ min$, Data input will contend with the data output because of the common I/O feature.



Page-Mode Cycle

Symbol	Parameter	Alternative Symbol	Limits								Unit
			MH25609-85		MH25609-10		MH25609-12		MH25609-15		
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{CPG}	Page-mode cycle time	t_{PC}	80		100		120		145		ns
$t_{W(CASH)}$	CAS high pulse width	t_{CP}	25		40		50		60		ns
t_{CPGRW}	Page-mode read-write cycle time	—	105		130		155		180		ns

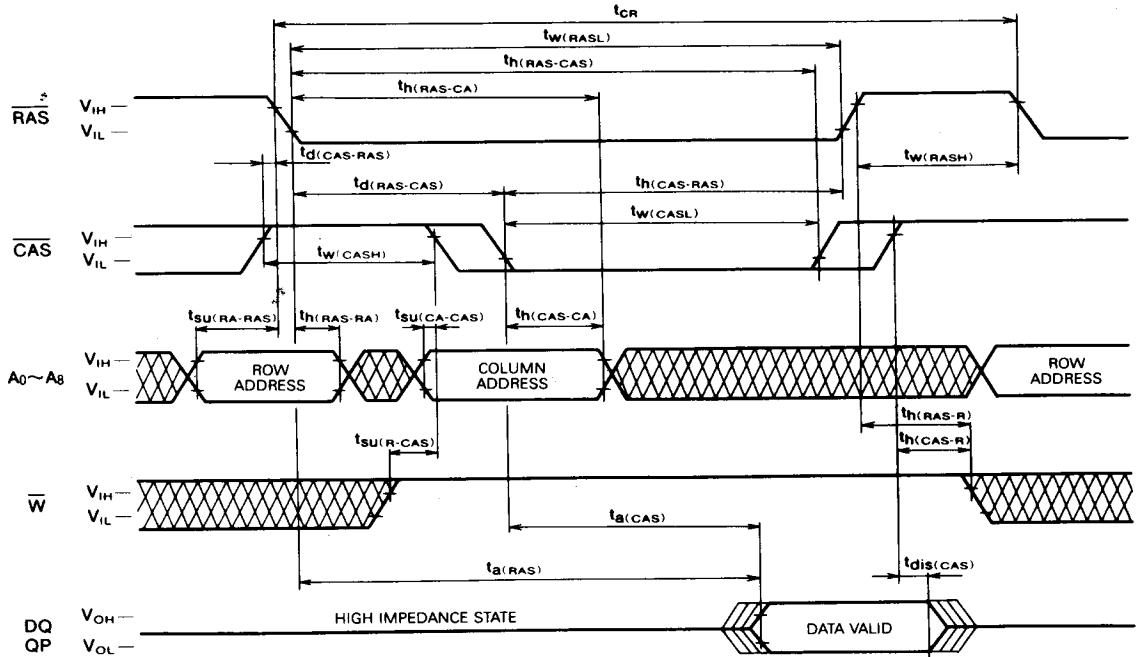
CAS before RAS Refresh Cycle (Note 16)

Symbol	Parameter	Alternative Symbol	Limits								Unit
			MH25609-85		MH25609-10		MH25609-12		MH25609-15		
			Min	Max	Min	Max	Min	Max	Min	Max	
$t_{SUR(CAS-RAS)}$	CAS setup time for auto refresh	t_{CSR}	10		10		10		10		ns
$t_{HR(RAS-CAS)}$	CAS hold time for auto refresh	t_{CHR}	15		20		25		30		ns
$t_{dR(RAS-CAS)}$	Precharge to CAS active time	t_{RPC}	0		0		0		0		ns

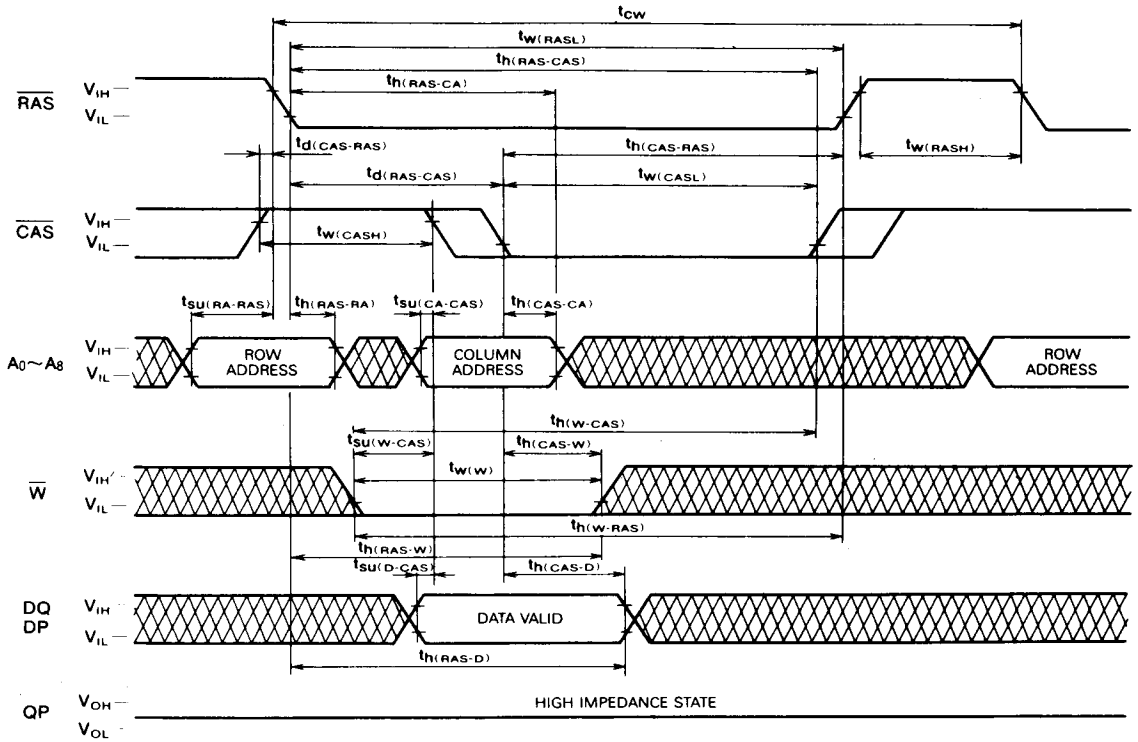
Note 16. Eight or more CAS before RAS cycles is necessary for proper operation of CAS before RAS refresh mode.

TIMING DIAGRAMS (Note 17)

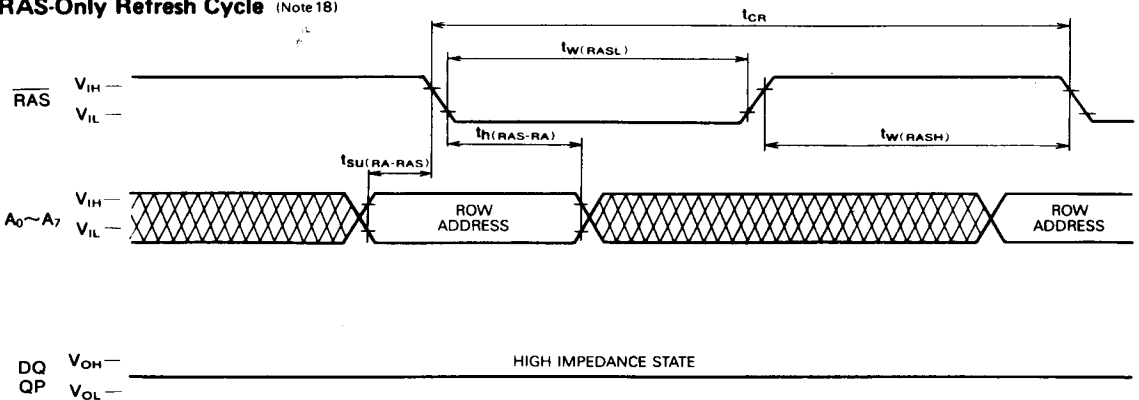
Read Cycle



Early Write Cycle



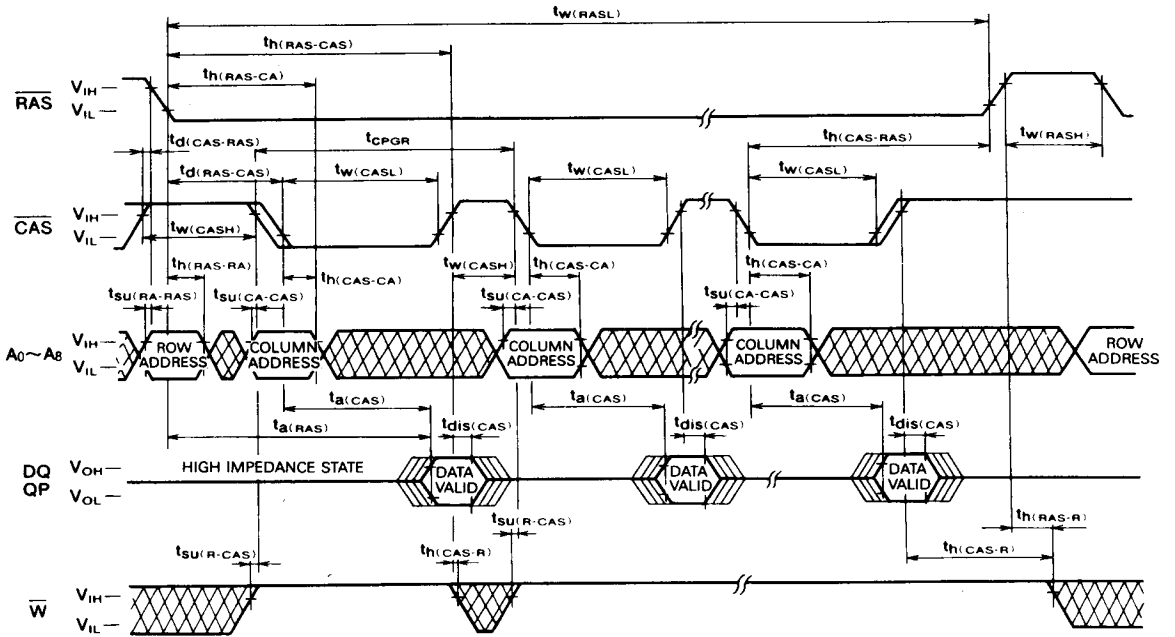
RAS-Only Refresh Cycle (Note 18)



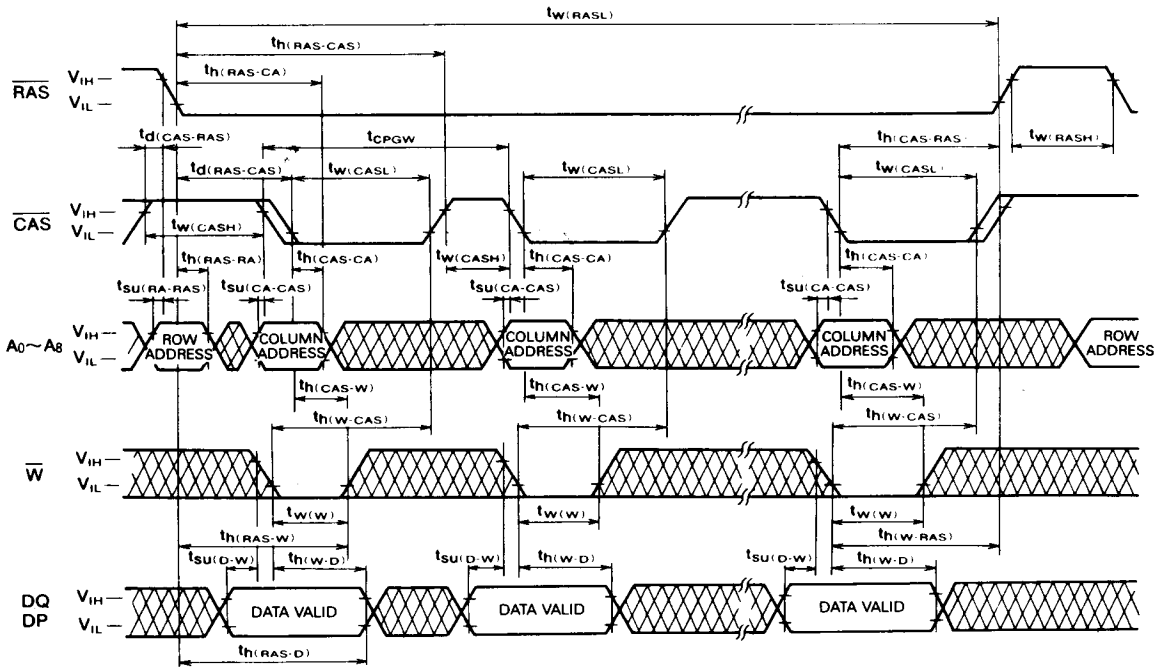
Note 17: Indicates the don't care input.
 The center-line indicates the high-impedance state.

Note 18: $\overline{CAS} = V_{IH}$, \overline{W} , D = don't care.
A8 may be V_{IH} or V_{IL} .

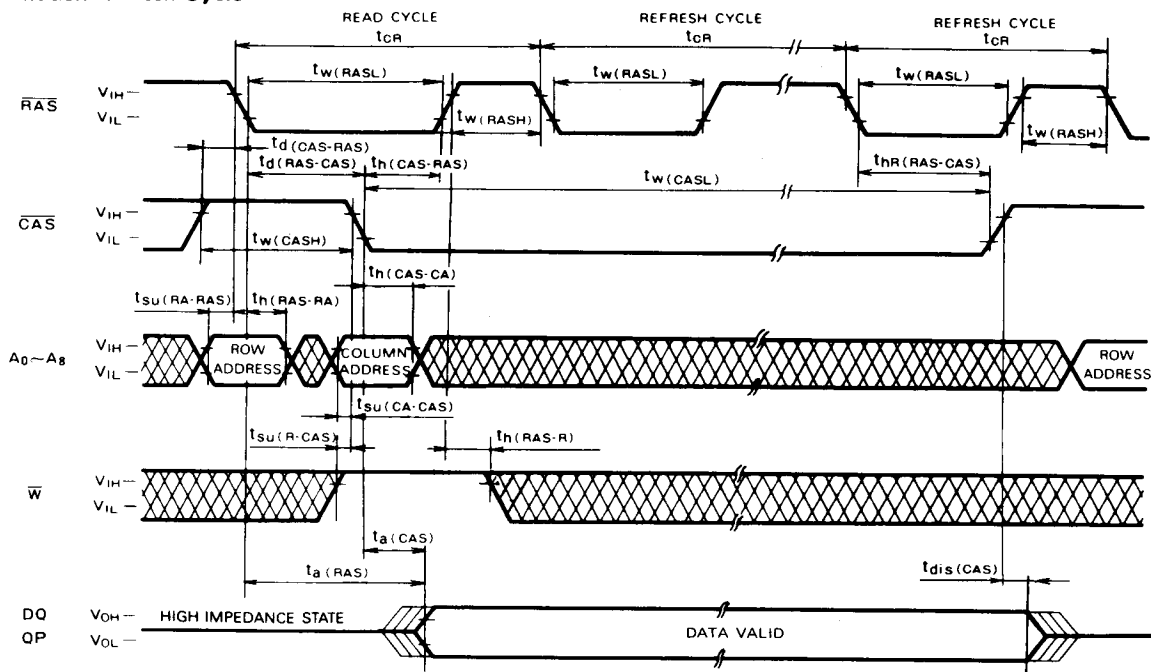
Page-Mode Read Cycle



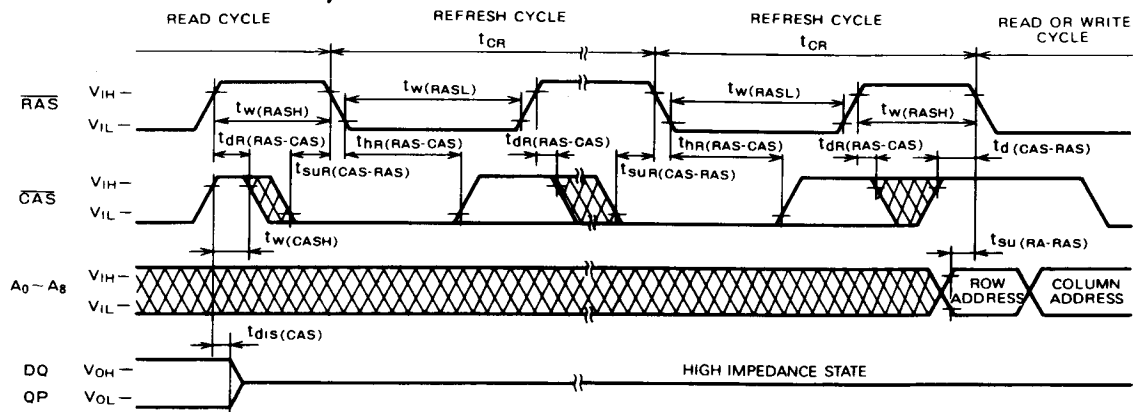
Page-Mode Write Cycle



Hidden Refresh Cycle



CAS before RAS Refresh Cycle (Note 19)



Note 19 $\bar{W}, D = \text{don't care}$.